## AMENDMENTS TO THE CLAIMS

The following listing of claims will replace all prior versions and listings of claims in the application.

## **LISTING OF CLAIMS**

1. (currently amended) A process for producing an organic semiconductor material having rodlike low-molecular liquid crystallinity, comprising: a skeleton structure comprising L 6  $\pi$  electron aromatic rings, M 10  $\pi$  electron aromatic rings, and N 14  $\pi$  electron aromatic rings, wherein L, M, and N are each an integer of 0 (zero) to 4 and L + M + N = 1 to 4; and a terminal structure attached to both ends of said skeleton structure, said terminal structure being capable of developing liquid crystallinity, said process comprising:

repeatedly purifying the organic semiconductor material to remove impurities such that the phase angle  $\theta$  of impedance of said organic semiconductor material is  $-80^{\circ} \leq \theta \leq -90^{\circ}$  as determined in the measurement of impedance in a frequency f range of 100 Hz  $\leq$  f  $\leq$  1 MHz in such a state that when said organic semiconductor material in an isotropic phase state is held between a pair of opposed substrates with an interelectrode spacing of 9  $\mu$ m.

Serial No. 10/698,002

2. (currently amended) An organic semiconductor element comprising a functional layer comprising an organic semiconductor material produced by the process according to claim 1, wherein

the organic semiconductor material, having rod-like low-molecular liquid crystallinity, comprises a skeleton structure comprising: L 6  $\pi$  electron aromatic rings, M 10  $\pi$  electron aromatic rings, and N 14  $\pi$  electron aromatic rings, wherein L, M, and N are each an integer of 0 (zero) to 4 and L + M + N = 1 to 4; and a terminal structure attached to both ends of said skeleton structure, said terminal structure being capable of developing liquid crystallinity.

the phase angle  $\theta$  of impedance of said organic semiconductor material is -80°  $\leq$   $\theta \leq$  -90° as determined in the measurement of impedance in a frequency f range of 100 Hz  $\leq$  f  $\leq$  1 MHz when said organic semiconductor material in an isotropic phase state is held between a pair of opposed substrates with an interelectrode spacing of 9  $\mu$ m, and

the functional layer has been formed by heating said organic semiconductor material to a temperature high enough for the organic semiconductor material to exhibit at least a smectic phase and then cooling the organic semiconductor material, and at least a part of the organic semiconductor material is in a crystal phase.

3. (currently amended) [[An]] <u>The</u> organic semiconductor element <del>comprising</del> a functional layer comprising an organic semiconductor material produced by the process according to claim [[1]] <u>2</u>, wherein

the organic semiconductor material exhibits a smectic phase.